
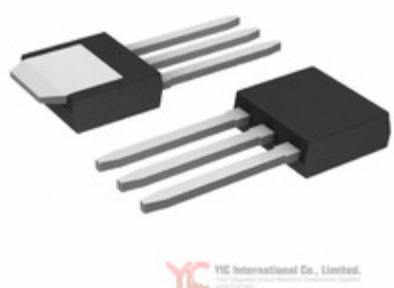
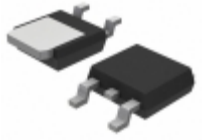
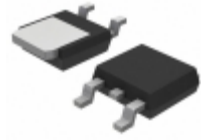
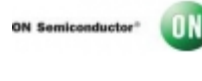

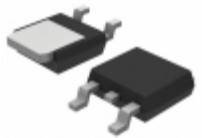



	<p>NTD4302-1G</p>
	<p>Hersteller-Teilenummer: NTD4302-1G</p> <p>Hersteller / Marke: AMI Semiconductor / ON Semiconductor</p> <p>Teil der Beschreibung: MOSFET N-CH 30V 8.4A IPAK</p> <p>Datenblätter:  NTD4302-1G.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 5000 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
	
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	NTD4302-1G
Hersteller	AMI Semiconductor / ON Semiconductor
Beschreibung	MOSFET N-CH 30V 8.4A IPAK
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	5000 pcs Stock
Serie	-
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Through Hole
Verpackung / Gehäuse	TO-251-3 Short Leads, IPak, TO-251AA
Supplier Device-Gehäuse	I-Pak
Verlustleistung (max)	1.04W (Ta), 75W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	30V
Strom - Ununterbrochener Abfluss (Id) bei 25 °C	8.4A (Ta), 68A (Tc)
Rds On (Max) @ Id, Vgs	10 mOhm @ 20A, 10V
VGS (th) (Max) @ Id	3V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	80nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	2400pF @ 24V
Verpackung	Tube


















































NTD4302-1G ist neu im Original, Suche NTD4302-1G Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie NTD4302-1G AMI Semiconductor / ON Semiconductor mit Garantie und Vertrauen. Anfrage NTD4302-1G: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>NTD4302T4 AMI Semiconductor / ON Semiconductor MOSFET N-CH 30V 8.4A DPAK</p>	 <p>NTD4302T4G AMI Semiconductor / ON Semiconductor MOSFET N-CH 30V 8.4A DPAK</p>	 <p>NTD40N05 AMI Semiconductor / ON Semiconductor NTD40N05 ON</p>	 <p>NTD4404N ON ON to251</p>
 <p>NTD4302G AMI Semiconductor / ON Semiconductor MOSFET N-CH 30V 8.4A DPAK</p>	 <p>NTD4404N1 ON ON TO-251</p>	 <p>NTD4302-001 ON NTD4302-001 ON</p>	 <p>NTD4302-001G VB NTD4302-001G VB</p>

heiße Teile

Mehr

 NTD30N02G	 NTD30N02T4	 NTD30N02T4G	 NTD30N06RT4	 NTD30N06T4G
 NTD32N06-001	 NTD32N06-1G	 NTD32N06G	 NTD32N06L	 NTD32N06L-001
 NTD32N06L-1G	 NTD32N06LG	 NTD32N06LT4G	 NTD32N06T4G	 NTD3808NT4G
 NTD3813NT4G	 NTD3817NT4G	 NTD40N03R	 NTD40N03R-1	 NTD40N03R-1G
 NTD40N03RG	 NTD40N03RT4	 NTD40N03RT4G	 NTD4302-001	 NTD4302-001G
 NTD4302G	 NTD4302T4	 NTD4302T4G	 NTD4804N	 NTD4804NT4G
 NTD4805N	 NTD4805N-1G	 NTD4805NT4G	 NTD4806N	 NTD4806N-35G
 NTD4806NA-35G	 NTD4806NG	 NTD4806NT4G	 NTD4808N	 NTD4808N-35G
 NTD4808NG	 NTD4808NT4G	 NTD4809N-35G	 NTD4809NAT4G	 NTD4809NH-35G
 NTD4809NHG	 NTD4809NHT4G	 NTD4809NT4G	 NTD4810N	 NTD4810N-1G

Contact us: Info@Y-IC.com

HINZUFÜGEN: Einheit A5-B5 Nr.509, 5 / F Sing Win Fabrikgebäude, 15-17 Shing Yip St, Kwun Tong, Kowloon, HongKong.

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